

CentralTM Semiconductor Corp.

145 Adams Avenue, Hauppauge, NY 11788 USA
Tel: (631) 435-1110 • Fax: (631) 435-1824

Manufacturers of World Class Discrete Semiconductors

2N1613
2N1711
2N1893

NPN Silicon Transistor

JEDEC TO-39 CASE

DESCRIPTION

The CENTRAL SEMICONDUCTOR 2N1613, 2N1711, and 2N1893 are Silicon NPN Planar Epitaxial Transistors designed for small signal general purpose and switching applications.

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

		2N1613	2N1711	2N1893	
Collector-Base Voltage	V_{CB0}	75	75	120	Vdc
Collector-Emitter Voltage	V_{CE0}	-	-	80	Vdc
Collector-Emitter Voltage	V_{CER}	50	50	100	Vdc
Emitter-Base Voltage	V_{EB0}	7.0	7.0	7.0	Vdc
Collector Current-Continuous	I_C		500		mAdc
Power Dissipation	P_T		0.8		watts
Power Dissipation, $T_C=25^{\circ}\text{C}$	P_T		3.0		watts
Operating and Storage	T_J, T_{stg}	-65 to $+200^{\circ}\text{C}$			
Junction Temperature					

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$)

Symbol	Test Conditions	2N1613		2N1711		2N1893		Unit
		Min	Max	Min	Max	Min	Max	
I_{CB0}	$V_{CB}=60\text{V}$	10		10		-		nA
I_{CB0}	$V_{CB}=90\text{V}$	-		-		10		nA
I_{EB0}	$V_{EB}=5.0\text{V}$	10		5		10		nA
BV_{CB0}	$I_C=100\mu\text{A}$	75		75		120		V
BV_{CE0}	$I_C=10\text{mA}$					80		V
BV_{CER}	$I_C=10\text{mA}$, $R_{BE}=10\text{ OHMS}$	50		50		100		V
BV_{EB0}	$I_E=100\mu\text{A}$	7.0		7.0		7.0		V
$V_{CE(s)}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$	-		-		1.2		V
$V_{CE(s)}$	$I_C=150\text{mA}$, $I_B=15\text{mA}$	1.5		1.5		5.0		V
$V_{BE(s)}$	$I_C=50\text{mA}$, $I_B=5\text{mA}$	-		-		0.9		V
$V_{BE(s)}$	$I_C=150\text{mA}$, $I_B=15\text{mA}$	1.3		1.3		1.3		V
h_{FE}	$V_{CE}=10\text{V}$, $I_C=10\mu\text{A}$	-		20		-		-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=100\mu\text{A}$	20		35		20		-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=10\text{mA}$	35		75		35		-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=150\text{mA}$	40	120	100	300	40	120	-
h_{FE}	$V_{CE}=10\text{V}$, $I_C=500\text{mA}$	20		40		-		-
f_T	$V_{CE}=10\text{V}$, 50mA , $f=20\text{ MHz}$	60		70		50		MHz
C_{ob}	$V_{CB}=10\text{V}$, $f=100\text{ KHz}$	25		25		15		pF
C_{ib}	$V_{BE}=0.5\text{V}$, $f=100\text{ KHz}$	80		80		85		pF
NF	$V_{CE}=10\text{V}$, $I_C=300\mu\text{A}$, $f=1.0\text{ KHz}$	12		8.0		-		dB